

Simultaneous AM-AM/AM-PM Distortion Measurements of Microwave Transistors Using Active Load-Pull and Six-Port Techniques

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A programmable active load-pull measurement system using two six-port reflectometers and three passive two-port standards has been developed to obtain load-pull contours of the transistor's input-output phase shift variations over a wide dynamic range of the input power. The output power, gain, power-added efficiency, and phase shift are measured simultaneously at the transistor's input and output reference planes. The phase distortion versus input power, $\Phi \sim P_{in}$, and the AM-PM conversion coefficient at various power levels, $k \sim P_{in}$, are obtained for different load impedances by post-measurement calculations. A NE8001 MESFET is tested at $f = 1.7$ GHz for the class A operation. The experimental results are also given.

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